

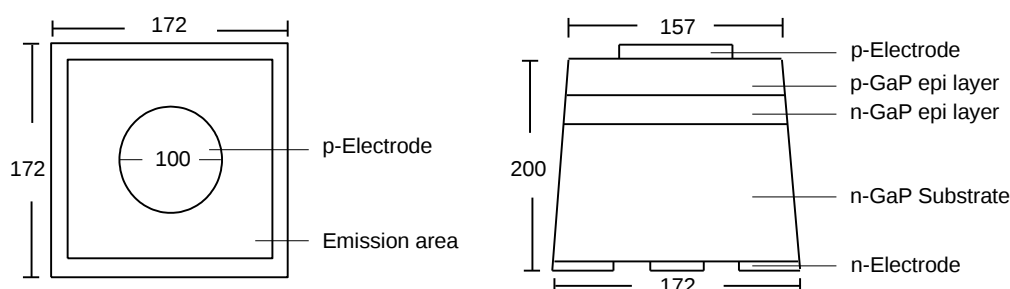
■ Features :

- GaP/GaP Epi Wafer

■ Typical Applications :

- Lamp
- SMD

■ Outline Dimensions : (Unit: um)



■ Physical Structure :

Chip dimension	Chip size	172 um x 172 um
	Thickness	200 um
	Emission area	157 um
	Bonding pad	100 um
Electrode	Top: P (anode)	Aluminum (Gold optional)
	Backside: N (cathode)	Gold alloy
Surface condition	Frosted	

■ Electro-Optical Characteristics : (Ta = 25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20 \text{ mA}$	1.90	2.40	2.60	V
Reverse Current	I_R	$V_R = 5 \text{ V}$	-	-	10	μA
Wavelength	λ_P	$I_F = 20 \text{ mA}$	-	568	-	nm
	Hue		570	573	574	
Spectral width at half height	$\Delta \lambda$	$I_F = 20 \text{ mA}$	-	30	-	nm
Luminous Intensity	I_v	$I_F = 20 \text{ mA}$	6.0	-	-	mcd

■ Typical Electro-Optical Characteristics Curve:

Fig 1. Forward Current vs. Forward Voltage

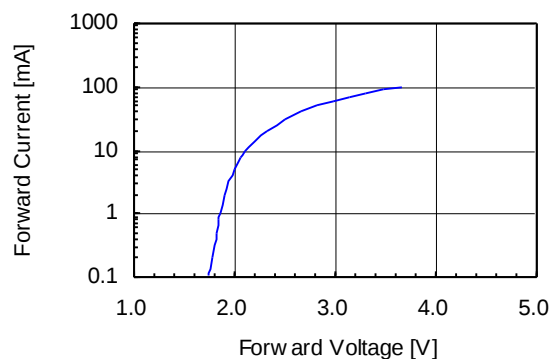


Fig 2. Relative Intensity vs. Forward Current

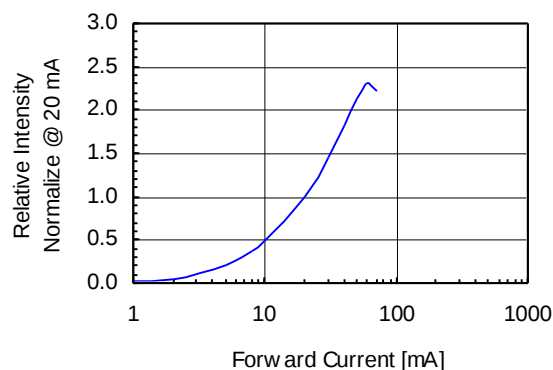


Fig 3. Forward Voltage vs. Temperature

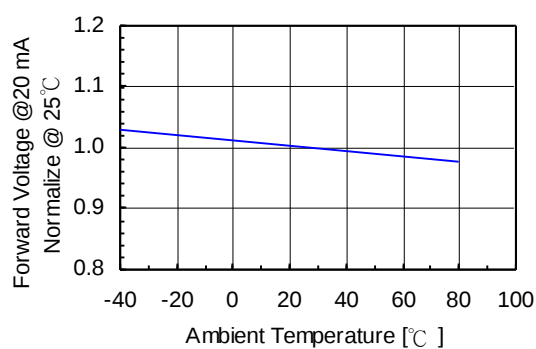


Fig 4. Relative Intensity vs. Temperature

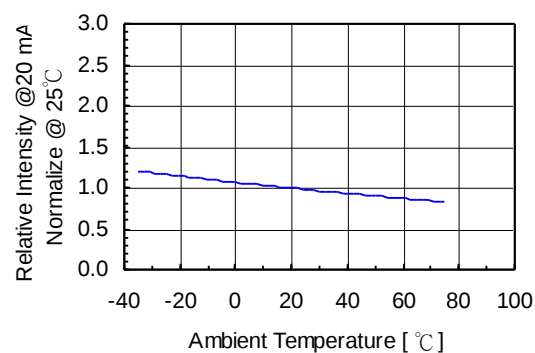


Fig 5. Relative Intensity vs. Wavelength

